

**X3-Class HiPerFET™  
Power MOSFET**
**IXFP36N20X3M**

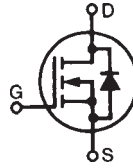
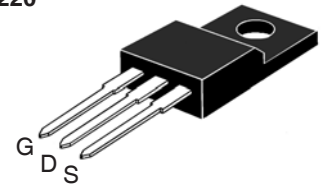
$$V_{DSS} = 200V$$

$$I_{D25} = 36A$$

$$R_{DS(on)} \leq 45m\Omega$$

**(Electrically Isolated Tab)**

N-Channel Enhancement Mode


**OVERMOLDED  
TO-220**

 G = Gate      D = Drain  
 S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	200	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	200	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$ , Limited by $T_{JM}$	36	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	50	A
$I_A$	$T_C = 25^\circ\text{C}$	18	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	300	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$	20	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	36	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
$M_d$	Mounting Torque	1.13 / 10	Nm/lb.in
<b>Weight</b>		2.5	g

**Features**

- International Standard Package
- Plastic Overmolded Tab
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu\text{A}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 500\mu\text{A}$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			5 $\mu\text{A}$ 100 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 18A$ , Note 1		38	45 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 18\text{A}$ , Note 1	16	26	S
$R_{Gi}$	Gate Input Resistance		1.6	$\Omega$
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		1425	pF
$C_{oss}$			280	pF
$C_{rss}$			1.2	pF
<b>Effective Output Capacitance</b>				
$C_{o(er)}$	Energy related	$V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \cdot V_{DSS}$	130	pF
$C_{o(tr)}$	Time related		400	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 18\text{A}$ $R_G = 30\Omega$ (External)		19	ns
$t_r$			30	ns
$t_{d(off)}$			54	ns
$t_f$			20	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 18\text{A}$		21	nC
$Q_{gs}$			8	nC
$Q_{gd}$			7	nC
$R_{thJC}$				3.5 $^\circ\text{C/W}$
$R_{thCS}$		0.50		$^\circ\text{C/W}$

### Source-Drain Diode

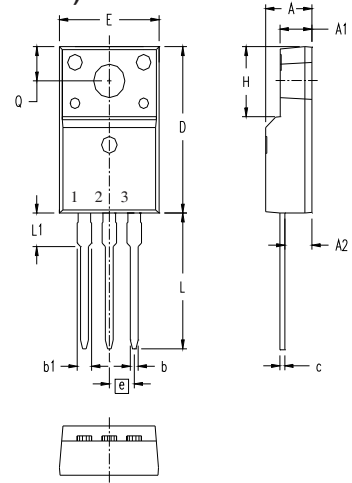
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$I_S$	$V_{GS} = 0\text{V}$			36 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			144 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	$I_F = 18\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		75	ns
$Q_{RM}$			230	nC
$I_{RM}$			6	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

### OVERMOLDED TO-220 (IXFP...M)

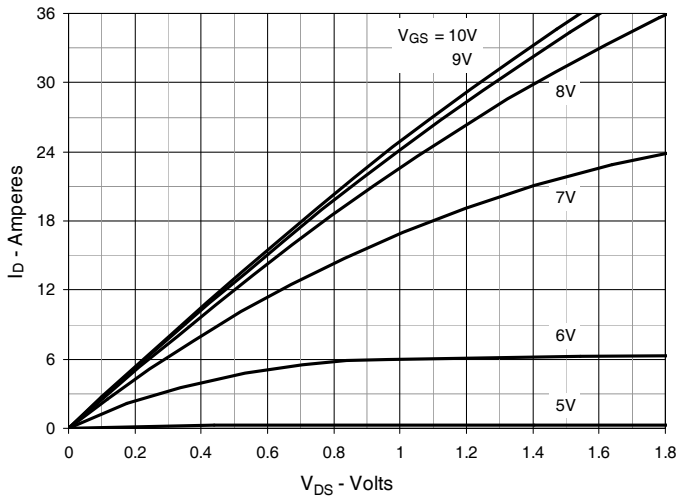
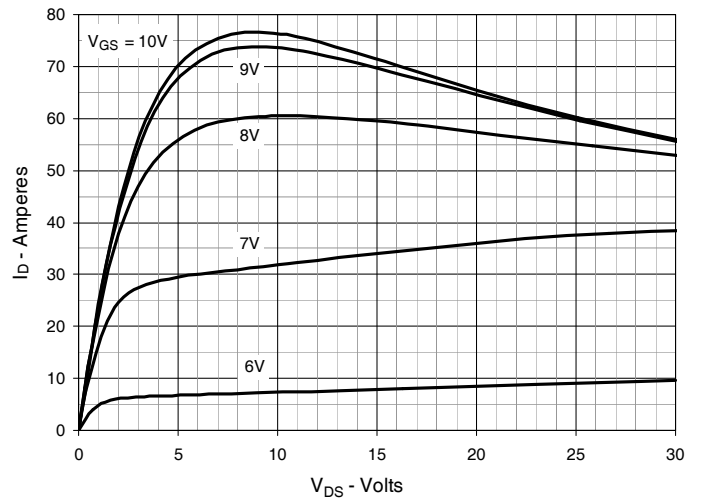
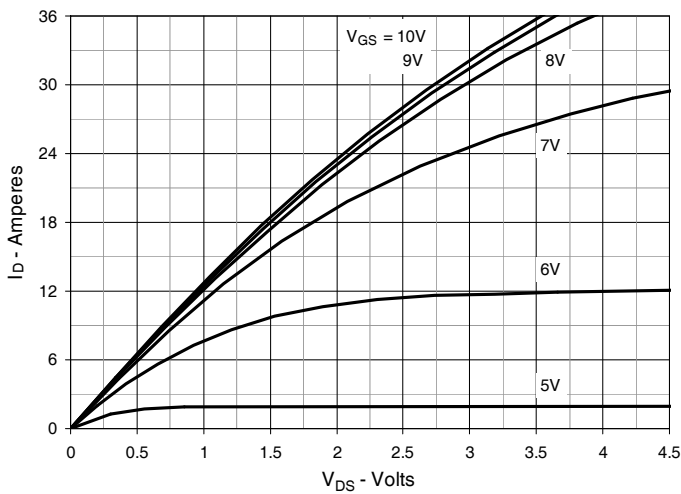
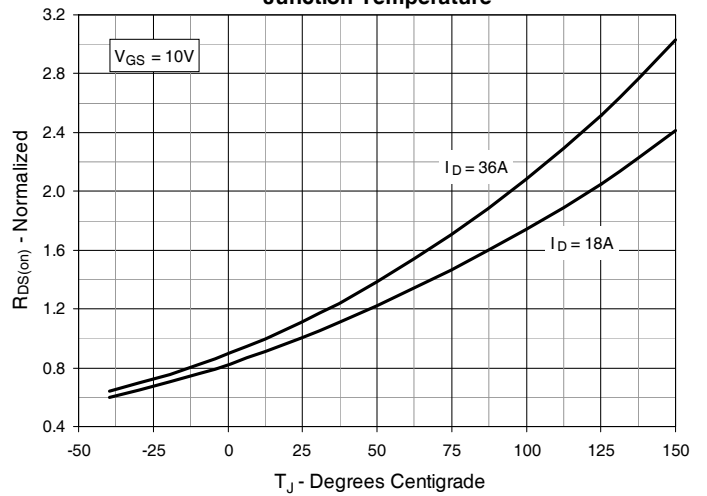
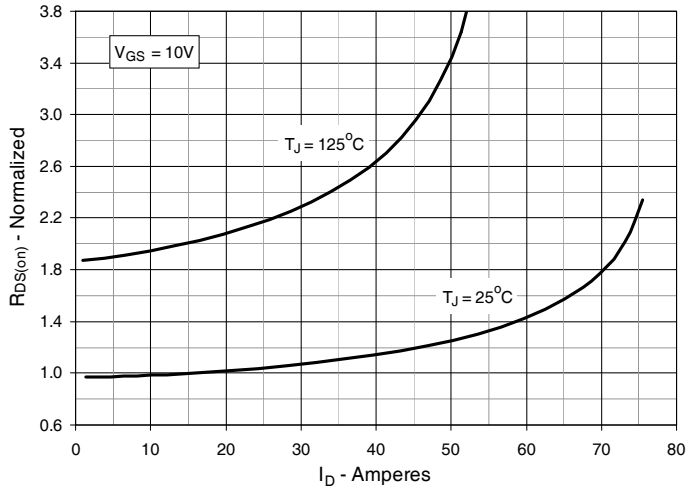
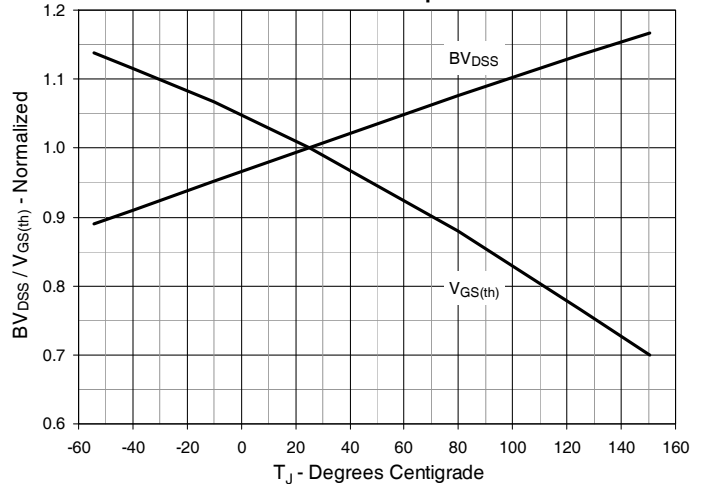


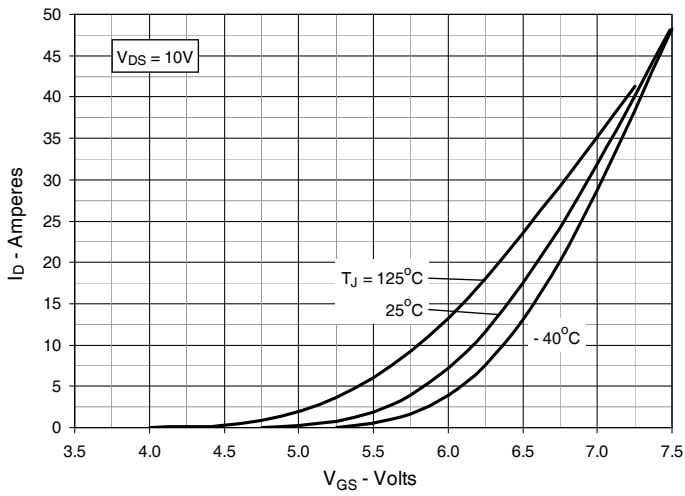
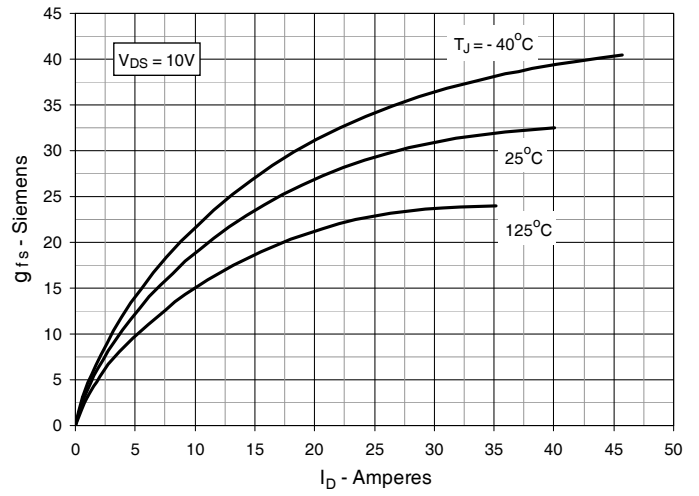
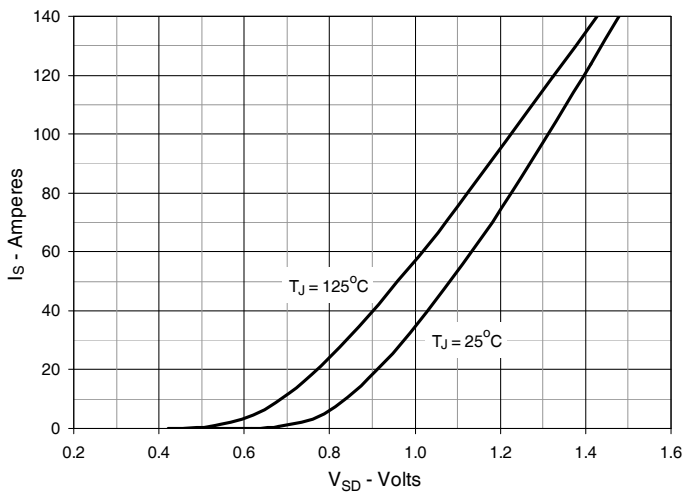
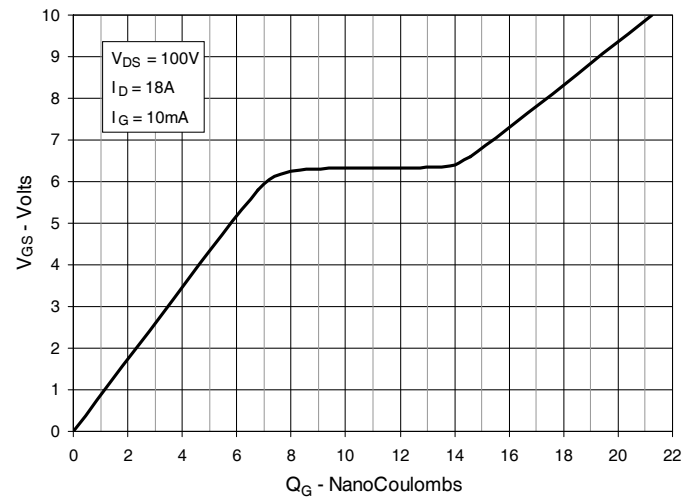
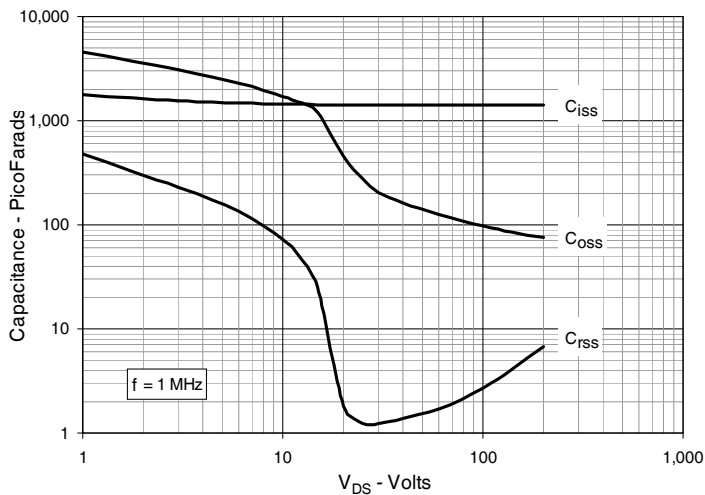
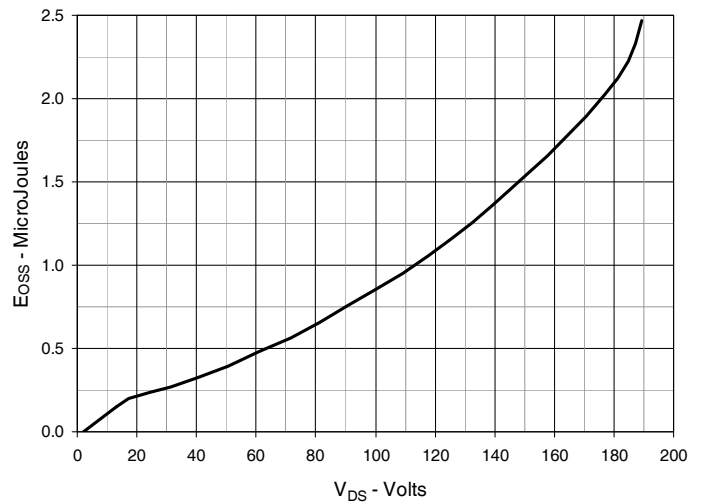
Terminals: 1 - Gate  
2 - Drain  
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
$\emptyset P$	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

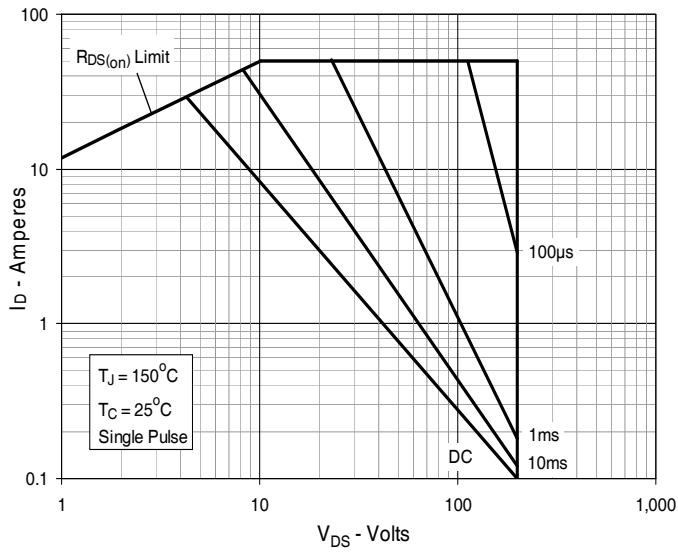
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 18\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 18\text{A}$  Value vs. Drain Current**

**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**


**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Output Capacitance Stored Energy**


**Fig. 13. Forward-Bias Safe Operating Area**



**Fig. 14. Maximum Transient Thermal Impedance**

